MM54HC155/MM74HC155 Dual 2-To-4 Line Decoder/Demultiplexers

General Description

The MM54HC155/MM74HC155 is a high speed silicon-gate CMOS decoder/demultiplexer. It utilizes advanced silicongate CMOS technology and features dual 1-line-to-4-line demultiplexers with independent strobes and common binary-address inputs. When both sections are enabled by the strobes, the common address inputs sequentially select and route associated input data to the appropriate output of each section. The individual strobes permit activating or inhibiting each of the 4-bit sections as desired. Data applied to input C1 is inverted at its outputs and data applied to C2 is non-inverted at its outputs. The inverter following the C1 data input permits use as a 3-to-8-line decoder, or 1-to-8line demultiplexer, without gating.

All inputs to the decoder are protected from damage due to electrostatic discharge by diodes to V_{CC} and Ground.

The device is capable of driving 10 low power Schottky TTL equivalent loads.

The MM54HC155/MM74HC155 is functionally and pin equivalent to the 54LS155/74LS155 with the advantage of reduced power consumption.

Features

■ Applications

Dual 2-to-4-line decoder

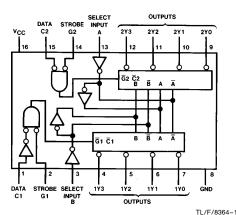
Dual 1-to-4-line demultiplexer

3-to-8-line decoder

1-to-8-line demultiplexer

- Typical propagation delay: 22 ns
- Low quiescent current: 80 µA maximum (74HC series)
- Wide operating range: 2V-6V

Connect and Logic Diagram



Order Number MM54HC155 or MM74HC155

Truth Tables 2-to-4-Line Decoder or 1-Line to 4-line Demultiplexer

	Inputs				puts	
Select	Strobe	Data				
ВА	G1	C1	1Y0	1Y1	1Y2	1Y3
ХХ	Н	Х	Н	Н	Н	Н
LL	L	Н	L	Н	Н	Н
LH	L	Н	Н	L	Н	Н
H L	L	Н	Н	Н	L	Н
н н	L	Н	Н	Н	Н	L
ХХ	X	L	Н	Н	Н	Н

	Inputs					Out	puts	
	Selec	:t	Strobe	Data				
	ВА	١	G2	C2	2Y0	2Y1	2Y2	2Y3
I	ХХ	`	Н	Х	Н	Н	Н	Н
	LL	.	L	L	L	Н	Н	Н
	L H	ı	L	L	Н	L	Н	Н
	H L	.	L	L	Н	Н	L	Н
1	н н	ł	L	L	Н	Н	Н	L
	ХХ	(X	Н	Н	Н	Н	Н

3-Line-to-8-Line Decoder or 1-l ine-to-8-l ine Demultiplexer

	Of 1-Line-to-o-Line Demuniplexer										
	Inputs				Outputs						
Se	ele	ct	Strobe Or Data	(0)	(1)	(2)	(3)	(4)	(5)	(6)	(7)
IC	В	Α	IG	2Y0	2Y1	2Y2	2Y3	1Y0	1Y1	1Y2	1Y3
Х	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н	Н
L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н
L	L	Н	L	Н	L	Н	Н	Н	Н	Н	Н
L	Н	L	L	Н	Н	L	Н	Н	Н	Н	Н
L	Н	Н	L	Н	Н	Н	L	Н	Н	Н	Н
Н	L	L	L	Н	Н	Н	Н	L	Н	Н	Н
Н	L	Н	L	Н	Н	Н	Н	Н	L	Н	Н
Н	Н	L	L	Н	Н	Н	Н	Н	Н	L	Н
Н	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	L

IC = inputs C1 and C2 connected together

IG = inputs G1 and G2 connected together
H = high level L = low level X = don't care

Absolute Maximum Ratings (Notes 1 and 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V _{CC})	-0.5V to $+7.0V$
DC Input Voltage (V _{IN})	$-$ 1.5V to $V_{\mbox{CC}}$ $+$ 1.5V
DC Output Voltage (V _{OUT})	-0.5 to $V_{\hbox{\footnotesize CC}}+0.5V$
Clamp Diode Current (I _{IK} , I _{OK})	20 mA
DC Output Current, per pin (IOUT)	25 mA
DC V _{CC} or GND Current, per Pin (I _{CC})	50 mA
Storage Temperature Range (T _{STG})	-65°C to +150°C

Power Dissipation (PD)

 (Note 3)
 600 mW

 S.O. Package only
 500 mW

 Lead Temp. (T_I) (Soldering 10 sec)
 260°C

Operating Conditions

		Min	Max	Unit
Supply Voltage (V	cc)	2	6	V
DC Input or Outpu	t Voltage			
(V_{IN}, V_{OUT})		0	V_{CC}	V
Operating Temper	ature Range (T _A)			
MM74HC		-40	+85	С
MM54HC		-55	+125	С
Input Rise/Fall Tir	$ne V_{CC} = 2.0V$		1000	ns
(t _r , t _f)	$V_{CC} = 4.5V$		500	ns
	$V_{CC} = 6.0V$		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	v _{cc}	T _A =	= 25°C	$T_{A} = -40^{\circ} \text{ to } +85^{\circ}\text{C}$	54HC T _A = - 55° to + 125°C	Units
				Тур		Guaranteed	l Limits	0
V _{IH}	Minimum High Level Input Voltage		2.0V 4.5V 6.0V		1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V V
V _{IL}	Maximum Low Level Input Voltage**		2.0V 4.5V 6.0V		0.5 1.35 1.8	0.5 1.35 1.8	0.5 1.35 1.8	V V
V _{OH}	Minimum High Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \ \mu\text{A}$	2.0V 4.5V 6.0V	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V V
		$\begin{aligned} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ \left I_{OUT} \right &\leq 4.0 \text{ mA} \\ \left I_{OUT} \right &\leq 5.2 \text{ mA} \end{aligned}$	4.5V 6.0V	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V
V _{OL}	Maximum Low Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $ I_{OUT} \le 20 \mu A$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V V V
		$ \begin{aligned} & V_{IN} = V_{IH} \text{ or } V_{IL} \\ & I_{OUT} \leq 4.0 \text{ mA} \\ & I_{OUT} \leq 5.2 \text{ mA} \end{aligned} $	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V
I _{IN}	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		±0.1	±1.0	±1.0	μΑ
Icc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		8.0	80	160	μΑ

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 3: Power Dissipation temperature derating — plastic "N" package: $-12 \text{ mW}/^{\circ}\text{C}$ from 65°C to 85°C; ceramic "J" package: $-12 \text{ mW}/^{\circ}\text{C}$ from 100°C to 125°. Note 4: For a power supply of 5V \pm 10% the worst case output voltages (V_{CH} and V_{CL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at $V_{\text{CC}} = 5.5 \text{V}$ and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN} , I_{CC} and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

Note 2: Unless otherwise specified, all voltages are referenced to ground.

^{**}V_{IL} limits are currently tested at 20% of V_{CC}. The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC}=5V, T_A=25^{\circ}C, C_L=15 \, pF, \, t_r=t_f=6 \; ns$

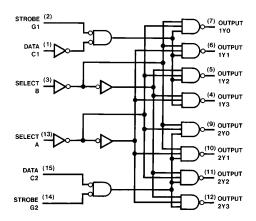
Symbol	Parameter	Conditions	Тур	Units
t _{PHL} , t _{PLH}	Maximum Propagation Delay, Binary Select to any Output 4 Levels of Delay		18	ns

AC Electrical Characteristics (Note 6) $C_L = 50$ pF, $t_{\text{f}} = 6$ ns (unless otherwise specified)

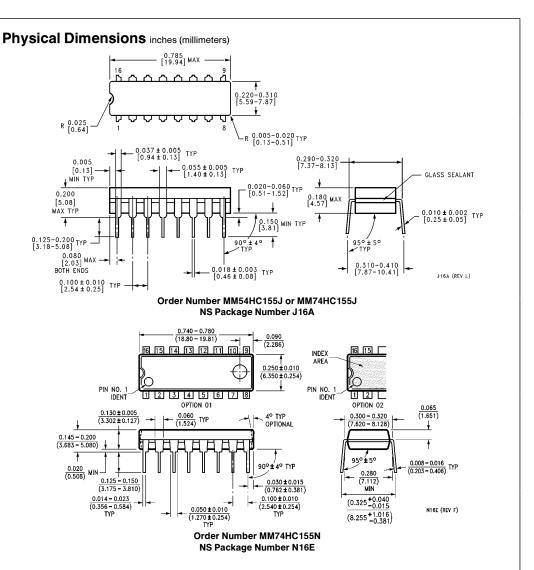
Symbol	Parameter	Conditions	v _{cc}	T _A = 25°C		74HC T _A = -40 to +85°C	54HC T _A = -55 to +125°C	Units
	Typ Guaranteed Limits		_imits					
t _{PHL} , t _{PLH}	Maximum Propagation Delay Binary Select to any Output 4 Levels of Delay		2.0V 4.5V 6.0	110 22 18	175 35 30	219 44 38	254 51 44	ns ns ns
t _{TLH} , t _{TLH}	Maximum Output Rise and FallTime		2.0V 4.5V 6.0V	30 8 7	75 15 13	95 19 16	110 22 19	ns ns ns
C _{IN}	Maximum Input Capacitance			3	10	10	10	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	(Note 5)		47				pF

Note 5: CPC determines the no load dynamic power consumption, $P_d = C_{PD} V_{CC}^2 f + I_{CC}$, and the no load dynamic current consumption, $I_S Q C_{PD} V_{CC} f + I_{CC}$.

Logic Diagram



TL/F/8364-2



LIFE SUPPORT POLICY

NATIONAL'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF THE PRESIDENT OF NATIONAL SEMICONDUCTOR CORPORATION. As used herein:

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.



National Semiconductor

National Semiconducto Corporation 1111 West Bardin Road Arlington, TX 76017 Tel: 1(800) 272-9959 Fax: 1(800) 737-7018

National Semiconductor Europe

Fax: (+49) 0-180-530 85 86 Fax: (+49) U-18U-35U oo oo Email: onjwege tevm2.nsc.com Deutsch Tel: (+49) 0-180-530 85 85 English Tei: (+49) 0-180-532 78 32 Français Tei: (+49) 0-180-532 93 58 Italiano Tel: (+49) 0-180-534 16 80 National Semiconductor

Hong Kong Ltd.
13th Floor, Straight Block,
Ocean Centre, 5 Canton Rd. Tsimshatsui, Kowloon Hong Kong Tel: (852) 2737-1600 Fax: (852) 2736-9960

National Semiconductor

Japan Ltd.
Tel: 81-043-299-2309
Fax: 81-043-299-2408